

#### Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT4401)
- Ideal for Medium Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

#### **Mechanical Data**

- Case: SOT23
- UL Flammability Rating 94V-0
- Case Material: Molded Plastic "Green" Compound
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (3)
- Weight: 0.008 grams (Approximate)

# Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMBT4403-7-F	Standard	K2T	7	8	3,000
MMBT4403-13-F	Standard	K2T	13	8	10,000

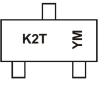
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**



 $\begin{array}{l} \mathsf{K2T} = \mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex:} \ \mathsf{I} = 2021) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex:} \ 9 = \mathsf{September}) \end{array}$ 

Date Code Key

Year	2003		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Р			J	K	L	М	Ν	0	Р	R	S
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-40	V
Collector-Emitter Voltage	Vceo	-40	V
Emitter-Base Voltage	Vebo	-6	V
Collector Current - Continuous (Note 7)	lc	-600	mA

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Collector Power Dissipation	(Note 5)	Da	310	mW
Collector Power Dissipation	(Note 6)	PD	350	TIVV
Thermal Desistance, Junction to Ambient	(Note 5)	Devi	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357	°C/W
Thermal Resistance, Junction to Leads	(Note 7)	R <sub>θJL</sub>	350	°C/W
Operating and Storage Temperature Range	TJ,TSTG	-55 to +150	°C	

400

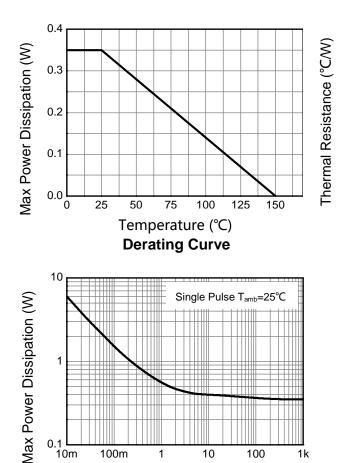
Notes:

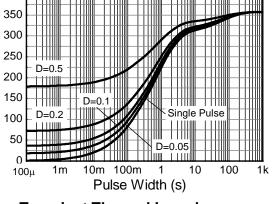
5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For the device mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).

### **Thermal Characteristics and Derating Information**





## **Transient Thermal Impedance**

Pulse Width (s)



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Oymbol		Max	Onit	Test condition
Collector-Base Breakdown Voltage	BVCBO	-40		V	$I_{\rm C} = -100 \mu A$ , $I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	BVCEO	-40		V	$I_{C} = -10 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	BVEBO	-6	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	ICEX	—	-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
Base Cutoff Current	IBL		-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
ON CHARACTERISTICS (Note 8)					• • • •
		30			$Ic = -100\mu A$ , $Vce = -1V$
		60			$I_{C} = -1.0 \text{mA}, V_{CE} = -1 \text{V}$
DC Current Gain	hfe	100	—	_	$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
		100	300		$I_{C} = -150 \text{mA}, V_{CE} = -2V$
		20	—		$I_{C} = -500 \text{mA}, V_{CE} = -2 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	-0.40	V	Ic = -150mA, I <sub>B</sub> = -15mA
	V CE(Sal)		-0.75		$I_{\rm C} = -500$ mA, $I_{\rm B} = -50$ mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-0.75	-0.95	V	Ic = -150mA, I <sub>B</sub> = -15mA
ç	V BE(Sal)		-1.30		Ic = -500mA, I <sub>B</sub> = -50mA
SMALL SIGNAL CHARACTERISTICS					1
Output Capacitance	Cobo		8.5	pF	$V_{CB} = -10V, f = 1.0MHz, I_E = 0$
Input Capacitance	Cibo		30	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	hie	1.5	15	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>	$V_{CE} = -10V, I_{C} = -1mA,$
Small Signal Current Gain	h <sub>fe</sub>	60	500	_	f = 1kHz
Output Admittance	hoe	1.0	100	μS	
Current Gain-Bandwidth Product	fτ	200	_	MHz	$V_{CE} = -10V, I_C = -20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS		-		-	-
Delay Time	td	—	15	ns	Vcc = -30V, Ic = -150mA,
Rise Time	tr		20	ns	$V_{BE(off)} = -2V$ , $I_{B1} = -15mA$
Storage Time	ts	_	225	ns	Vcc = -30V, Ic = -150mA,
Fall Time	tr	_	30	ns	I <sub>B1</sub> = -I <sub>B2</sub> = -15mA

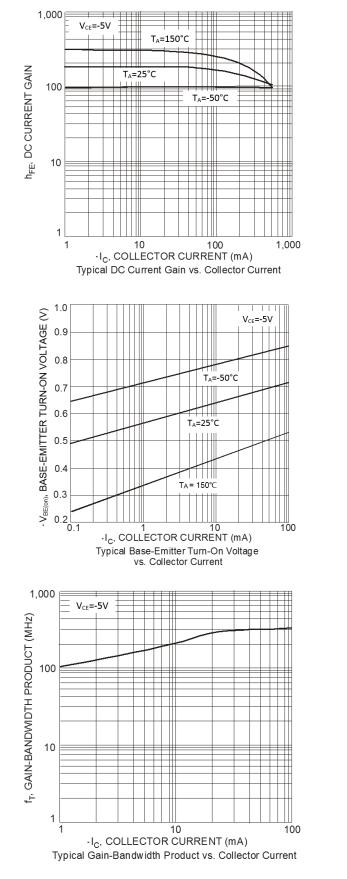
Note:

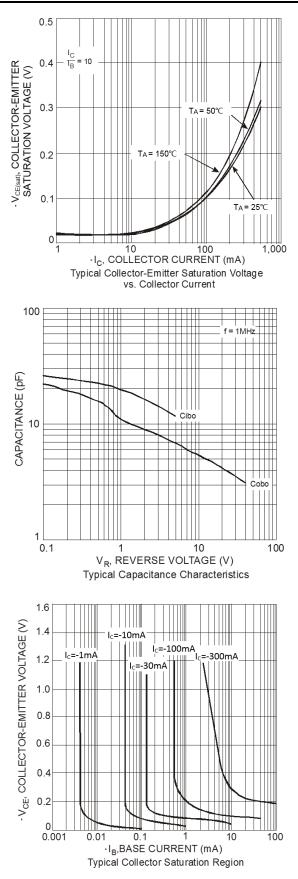
8. Short duration pulse test used to minimize self-heating effect.



**MMBT4403** 

### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

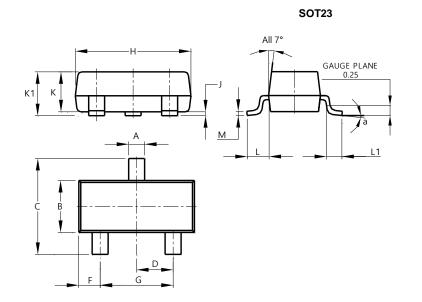






# **Package Outline Dimensions**

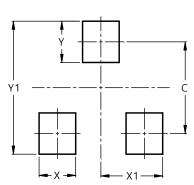
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
Μ	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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